ABSTRACT OF THE DISCLOSURE

A field effect transistor includes an n^+ high-density impurity injection area, a p^+ high-density impurity injection area, an i-impurity non-injection area, and a gate electrode. The gate electrode is free from completely lapping over the i-impurity non-injection area, but laps over substantially half the i-impurity non-injection area adjacent to the n^+ high-density impurity injection area so as to avoid channel carrier capture levels due to crystal defects/grain boundaries and an effect of potential barriers due to the channel carrier capture levels.